

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TENT APPLICATION of

Group Art Unit: 1745

Appln. Ser. No.: 09/501,622

Secret Committee: Kalafut for the

Secret Committee

Filing Date: 02/09/2000

Title: DOPED SEMICONDUCTOR AND METHOD OF MAKING THE DOPED

SEMICONDUCTOR

July 26, 2005

NEW INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Attached are PTO/SB/O8B forms listing the enclosed documents. Copies of the enclosed documents are attached to the presently filed Information Disclosure Statement and/or to the Attachments to the Response filed herewith.

Applicant advises the Secret Committee that took over examination of his pending applications relating to his lower-energy hydrogen technology that Applicant has made a concerted effort to review those applications for documents cited therein and to make those documents of record in each case. Because, however, Applicant's lower-energy hydrogen applications were consolidated under a single Examiner. Bernard Eng-Kie Souw, Applicant believes that the Committee should already be familiar with the totality of these documents. Nonetheless, for purposes of completeness and ensuring that all cited documents have been brought to the PTO's attention, Applicant provides the following list of applications relating to his lower-energy

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